UF28100V



RF Power MOSFET Transistor 100W, 100-500 MHz, 28V

M/A-COM Products Released; RoHS Compliant

Features

- N-channel enhancement mode device
- DMOS structure
- Lower capacitances for broadband operation
- High saturated output power
- Lower noise figure than competitive devices

ABSOLUTE MAXIMUM RATINGS AT 25° C

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V_{DS}	65	V
Gate-Source Voltage	V _{GS}	20	V
Drain-Source Current	I _{DS}	12*	Α
Power Dissipation	P _D	250	W
Junction Temperature	TJ	200	°C
Storage Temperature	T _{STG}	-55 to +150	°C
Thermal Resistance	θ_{JC}	0.7	°C/W

TYPICAL DEVICE IMPEDANCES

F (MHz)	Z _{IN} (Ω)	Z _{LOAD} (Ω)			
100	4.5-j6.0	14.5+j0.5			
300	2.25-j1.75	7.5j1.0			
500	1.5+j5.5	3.5+j3.5			
V _{DD} =28V, I _{DQ} =600 Ma, P _{OUT} =100.0 W					

Z_{IN} is the series equivalent input impedance of the device from gate to gate.

Z_{LOAD} is the optimum series equivalent load impedance as measured from drain to drain.

FLECTRICAL CHARACTERISTICS AT 25°C

Parameter	Symbol	Min	Max	Units	Test Conditions
Drain-Source Breakdown Voltage	BV _{DSS}	65	-	V	V _{GS} = 0.0 V , I _{DS} = 15.0 mA
Drain-Source Leakage Current	I _{DSS}	-	3.0	mA	V _{GS} = 28.0 V , V _{GS} = 0.0 V
Gate-Source Leakage Current	I _{GSS}	-	3.0	μΑ	V _{GS} = 20.0 V , V _{DS} = 0.0 V
Gate Threshold Voltage	V _{GS(TH)}	2.0	6.0	V	V _{DS} = 10.0 V , I _{DS} = 300.0 mA
Forward Transconductance	G _M	1.5	-	S	V_{DS} = 10.0 V , I_{DS} 3000.0 mA , Δ V_{GS} = 1.0V, 80 μs Pulse
Input Capacitance	C _{ISS}	-	135	pF	V _{DS} = 28.0 V , F = 1.0 MHz
Output Capacitance	Coss	-	90	pF	V _{DS} = 28.0 V , F = 1.0 MHz
Reverse Capacitance	C _{RSS}	-	24	pF	V _{DS} = 28.0 V , F = 1.0 MHz
Power Gain	G _P	10	-	dB	V _{DD} = 28.0 V, I _{DQ} = 600.0 mA, P _{OUT} = 100.0 W F =500 MHz
Drain Efficiency	ŋ _D	50	-	%	V _{DD} = 28.0 V, I _{DQ} = 600.0 mA, P _{OUT} = 100.0 W F =500 MHz
Return Loss	R_L	10	-	dB	V _{DD} = 28.0 V, I _{DQ} = 600.0 mA, P _{OUT} = 100.0 W F =500 MHz
Load Mismatch Tolerance	VSWR-T	-	30:1	-	V_{DD} = 28.0 V, I_{DQ} = 600.0 mA, P_{OUT} = 100.0 W F =500 MHz

*Per side

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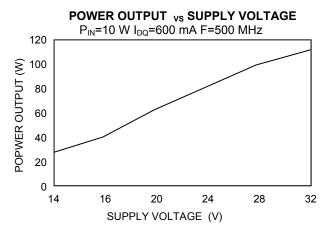


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Typical Broadband Performance Curves

STREQUENCY To Street Street



V_{DD} =28 V I_{DQ} =600 mA (Push pull device) 120 200MHz 400MHz 500MHz 40 MOd 20

4

POWER INPUT (W)

8

10

12

2

POWER OUTPUT _{vs} POWER INPUT

0

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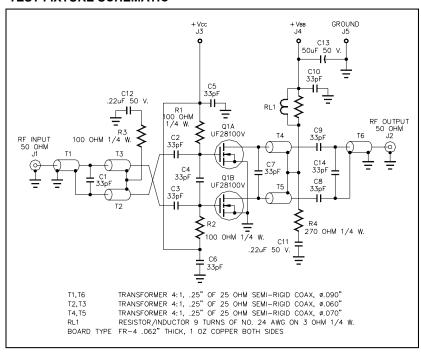
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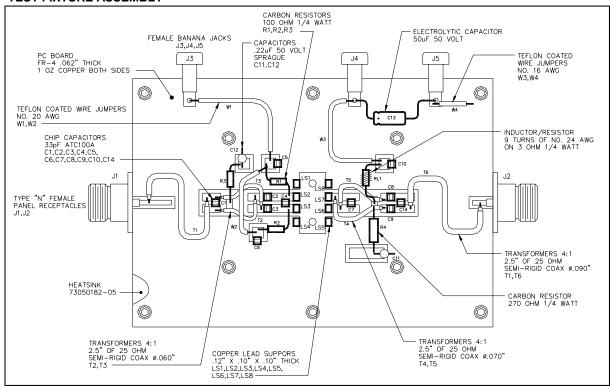
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TEST FIXTURE SCHEMATIC



TEST FIXTURE ASSEMBLY



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